Product data sheet

1. General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Isolated plastic package
- Low thermal resistance
- Low reverse recovery current
- · Reduces switching losses in associated MOSFET

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies
- Half-bridge lighting ballasts

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		600			V	
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _h = 47 °C; Fig. 1; Fig. 2	8			А	
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μs; T_h ≤ 47 °C; square-wave pulse	16			А	
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 3	55		А		
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	60		А		
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics						
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 4</u>		-	2	2.9	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>		-	1.5	1.85	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$		-	20	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode		K — A
mb	n.c.	mounting base; isolated	1 2 SOD113 (2-lead TO-220F)	001aaa020

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYC8DX-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113			

7. Marking

Table 4. Marking codes

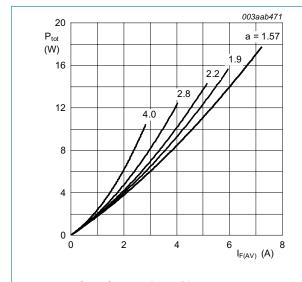
Type number	Marking codes
BYC8DX-600	BYC8DX-600

8. Limiting values

Table 5. Limiting values

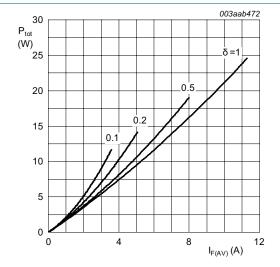
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; T _h = 47 °C; Fig. 1; Fig. 2	8	Α
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_h \le 47 °C$; square-wave pulse	16	Α
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	55	Α
	forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	60	Α
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C



a = form factor = $I_{F(RMS)}/I_{F(AV)}$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance	without heatsink compound	-	-	7.2	K/W
	from junction to heatsink	with heatsink compound; Fig 3	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

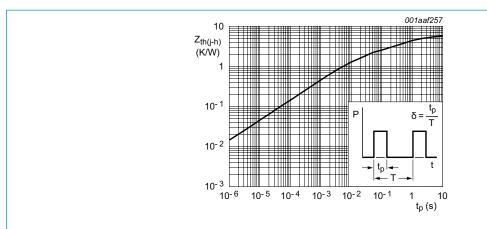


Fig. 3. Transient thermal impedance from junction to heatsink as a function of pulse width

10. Isolation characteristics

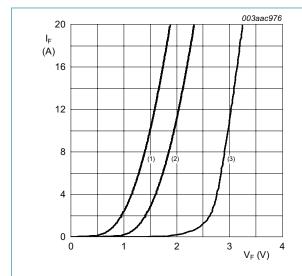
Table 7. Isolation characteristics

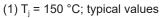
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(RMS)}$	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink	-	10	-	pF

11. Characteristics

Table 8. Characteristics

	Taracteristics	0				11.32
Symbol	Parameter	Conditions	Miı	1 Typ	Max	Unit
Static cha	racteristics					
V_{F}	forward voltage	$I_F = 8 \text{ A}; T_j = 25 \text{ °C}; Fig. 4$	-	2	2.9	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	1.5	1.85	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	9	40	μA
		V _R = 500 V; T _j = 100 °C	-	1.1	3	mA
Dynamic	characteristics					·
Q _r	recovered charge	$I_F = 1 \text{ A}; V_R = 100 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$	-	13	-	nC
t _{rr} revers	reverse recovery time	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 100 \text{ °C}; \underline{\text{Fig. 5}}$	-	32	40	ns
		$I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 50 \text{ A/}\mu\text{s;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 5}}{}$	-	30	52	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5$		20	-	ns
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 100 ^{\circ}\text{C}$	-	9.5	12	А
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}$	-	1.5	5.5	А
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 6}}{}$	-	8	10	V





(2) $T_i = 150$ °C; maximum values

(3) T_i = 25 °C; maximum values



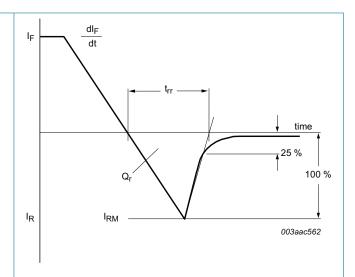
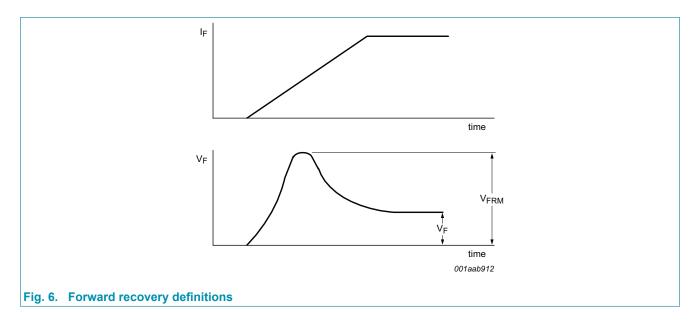


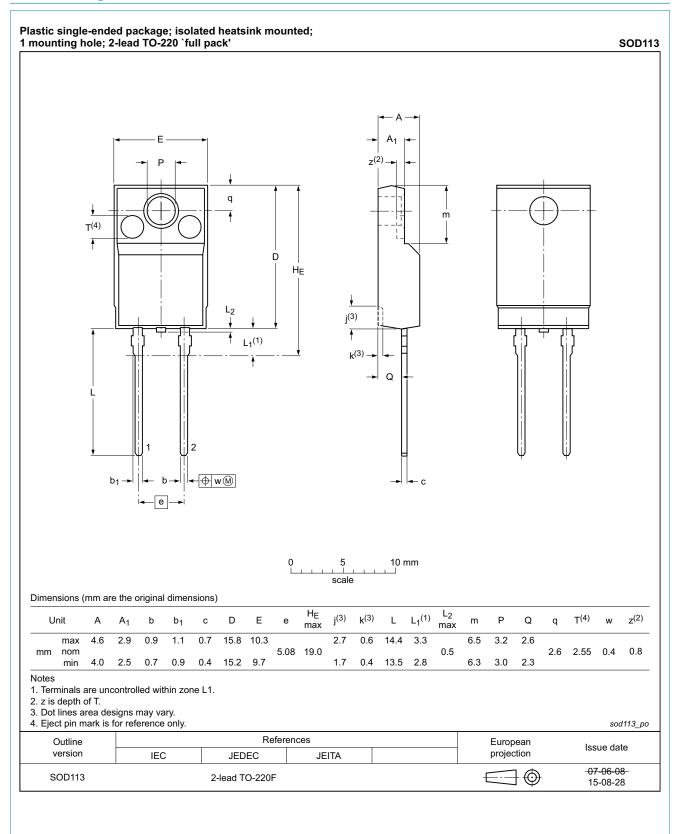
Fig. 5. Reverse recovery definitions; ramp recovery

WeEn Semiconductors

Hyperfast power diode



12. Package outline



13. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
BYC8DX-600 v.2	20180129	Product data sheet	-	BYC8DX-600 v.1			
Modifications:	Modifications: Change from NXP version to WeEn version						
BYC8DX-600 v.1	20101227	Product data sheet	-	-			

14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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15. Contents

1. General description	
2. Features and benefits	
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	4
10. Isolation characteristics	4
11. Characteristics	
12. Package outline	7
13. Revision hihstory	
14. Legal information	9
15. Contents	11

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